

a second conductivity type cladding layer containing Al as a group III element and formed with a ridge portion;

β^1 a current blocking layer, formed on said second conductivity type cladding layer around said ridge portion, containing Al as a group III element in this order, wherein

an angle θ of inclination on a side surface of said ridge portion with respect to an upper surface of said substrate is at least 70° and not more than 117° ,

a distance t between said emission layer and said current blocking layer satisfies a relation of $t \leq 0.275/(1 - (X2 - X1))$ micrometer assuming that $X1$ represents a composition ratio of Al in group III elements forming said second conductivity type cladding layer, $X2$ represents a composition ratio of Al in group III elements forming said current blocking layer, and

a lower width W of said ridge portion is at least $2 \mu\text{m}$ and not more than $5 \mu\text{m}$.

β^2 4. **(Twice Amended)** The semiconductor laser device according to claim 1, wherein said distance t between said emission layer and said current blocking layer satisfies a relation of $t \leq 0.252/(1 - (X2 - X1))$ micrometer.
